Figure 2 - Formation of \{105\} facets from shapeless areas with excess of Ge:

STM images of different phases of faceting, $T_{gr} = 650^\circ$C, $h_{Ge} = 5$ Å; (a) a shapeless Ge ‘heap’ without faceting, 150 × 141 nm; (b) at the outset of faceting, 64 × 64 nm; (c)–(d) after growth stoppage and annealing at the growth temperature; (c) 72 × 72 nm; (d) 46 × 46 nm; (e) 23 × 23 nm.